

L Number	Hits	Search Text	DB	Time stamp
18	5	((("6081009") or ("5438215") or ("6566709") or ("6498367") or ("5594261"))).PN.	USPAT	2003/06/17 11:19
19	6	((("6081009") or ("5438215") or ("6566709") or ("6498367") or ("5594261") or ("5886383"))).PN.	USPAT	2003/06/17 10:49
20	11	((("6081009") or ("5438215") or ("6566709") or ("6498367") or ("5594261") or ("5886383") or ("5396085") or ("5416354") or ("5719411") or ("5818084") or ("5877515"))).PN.	USPAT	2003/06/17 10:49
21	672	(257/341).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:53
22	209	(257/495).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:53
23	402	(257/653).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:53
24	1188	(257/401).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
25	359	(257/342).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
26	345	(257/139).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
27	284	(257/133).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
28	103	(257/149).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
29	351	(257/147).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
30	175	(257/155).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:54
31	1257	(257/355).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55

32	104	(257/135).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55
33	101	(257/168).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55
34	725	(257/409).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:55
35	1531	257/168,409,341,495,653,401,342,139,133,149 and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))	USPAT;155,352 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 11:07
36	1184	(257/168,409,341,495,653,401,342,139,133,149 and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209	USPAT;155,352 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 11:09
37	28	((257/168,409,341,495,653,401,342,139,133,149 and (first adj (conductivity or impurity or ions)) and (second adj (conductivity or impurity or ions))) and @ad<=19981209) and (edg\$4 adj (structures or device))	USPAT;155,352 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 11:11
-	855	high adj voltage adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:45
-	97	(257/168).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/17 10:53
-	708	(257/409).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/08 14:37
-	18	(high adj voltage adj semiconductor) same (edg\$3 adj (structure or device))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 10:12
-	1	("20020005733").PN.	USPAT; US-PGPUB	2003/01/09 10:12